

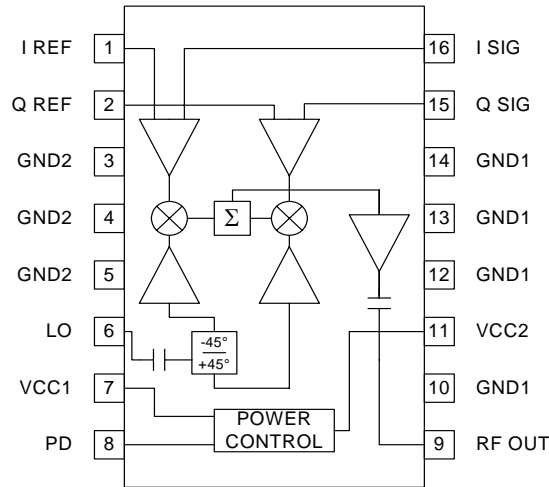


**Features**

- Typical Carrier Suppression > 35 dBc over temperature with highly linear operation
- Single 5V Power Supply
- Integrated RF quadrature network
- Digitally controlled Power Down mode
- 800MHz to 2500MHz operation

**Applications**

- Dual-Band CDMA Base Stations
- TDMA/TDMA-EDGE Base Stations
- GSM-EDGE/EGSM Base Stations
- W-CDMA Base Stations
- WLAN and WLL Systems
- TETRA Systems



Functional Block Diagram

**Product Description**

The RF2480 is a monolithic integrated quadrature modulator IC capable of universal direct modulation for high-frequency AM, PM, or compound carriers. This low-cost IC features excellent linearity, noise floor, and over-temperature carrier suppression performance. The device implements differential amplifiers for the modulation inputs, 90° carrier phase shift network, carrier limiting amplifiers, two matched double-balanced mixers, summing amplifier, and an output RF amplifier which will drive 50Ω from 800MHz to 2500MHz. Component matching is used to obtain excellent amplitude balance and phase accuracy.

**Ordering Information**

|             |                                  |
|-------------|----------------------------------|
| RF2480      | Direct Quadrature Modulator      |
| RF2480 PCBA | Fully Assembled Evaluation Board |

**Optimum Technology Matching® Applied**

- |  |                                      |                                     |                                   |
|--|--------------------------------------|-------------------------------------|-----------------------------------|
| <input checked="" type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET         | <input type="checkbox"/> Si BiCMOS   | <input type="checkbox"/> Si CMOS    |                                   |
| <input type="checkbox"/> InGaP HBT           | <input type="checkbox"/> SiGe HBT    | <input type="checkbox"/> Si BJT     |                                   |

RF MICRO DEVICES®, RFMD®, Optimum Technology Matching®, Enabling Wireless Connectivity™, PowerStar®, POLARIS™ TOTAL RADIO™ and UltimateBlue™ are trademarks of RFMD, LLC. BLUETOOTH is a trademark owned by Bluetooth SIG, Inc., U.S.A. and licensed for use by RFMD. All other trade names, trademarks and registered trademarks are the property of their respective owners. ©2006, RF Micro Devices, Inc.

## Absolute Maximum Ratings

| Parameter                     | Rating       | Unit            |
|-------------------------------|--------------|-----------------|
| Supply Voltage                | -0.5 to +7.5 | V <sub>DC</sub> |
| Input LO and RF Levels        | +10          | dBm             |
| Operating Ambient Temperature | -40 to +85   | °C              |
| Storage Temperature           | -40 to +150  | °C              |



**Caution!** ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

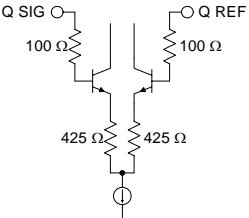
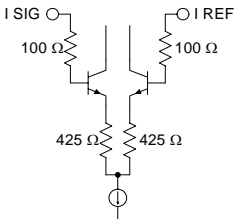
RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

The information in this publication is believed to be accurate and reliable. However, no responsibility is assumed by RF Micro Devices, Inc. ("RFMD") for its use, nor for any infringement of patents, or other rights of third parties, resulting from its use. No license is granted by implication or otherwise under any patent or patent rights of RFMD. RFMD reserves the right to change component circuitry, recommended application circuitry and specifications at any time without prior notice.

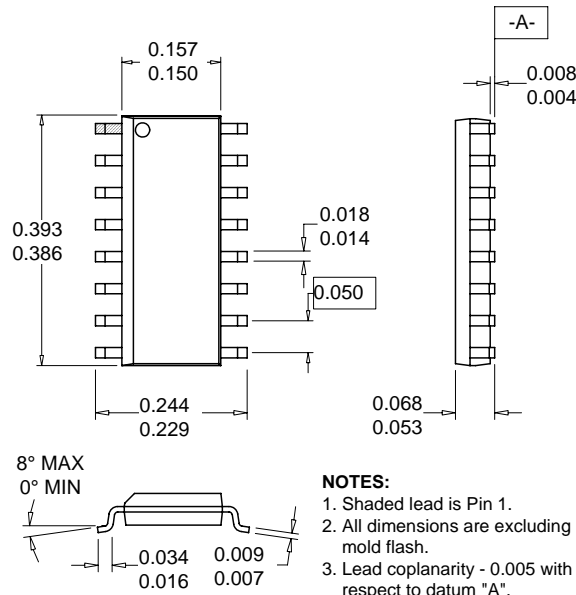
| Parameter                             | Specification |       |                       | Unit   | Condition   |
|---------------------------------------|---------------|-------|-----------------------|--------|---|
|                                       | Min.          | Typ.  | Max.                  |        |   |
| <b>Carrier Input</b>                  |               |       |                       |        | T=25°C, V <sub>CC</sub> =5V   |
| Frequency Range                       | 800           |       | 2500                  | MHz    |   |
| Power Level                           | -6            |       | +6                    | dBm    |   |
| Input VSWR                            |               | 4.5:1 |                       |        | At 900MHz unmatched   |
|                                       |               | 2:1   |                       |        | At 1800MHz unmatched  |
|                                       |               | 2:1   |                       |        | At 2500MHz unmatched  |
| <b>Modulation Input</b>               |               |       |                       |        |   |
| Frequency Range                       | DC            |       | 250                   | MHz    |   |
| Reference Voltage (V <sub>REF</sub> ) |               | 3.0   |                       | V      |   |
| Maximum Modulation (I&Q)              |               |       | V <sub>REF</sub> ±1.0 | V      |   |
| Gain Asymmetry                        |               | 0.2   |                       | dB     |   |
| Quadrature Phase Error                |               | 3     |                       | °      |   |
| Input Resistance                      |               | 30    |                       | kΩ     |   |
| Input Bias Current                    |               |       | 40                    | μA     |   |
| <b>RF Output (~800MHz)</b>            |               |       |                       |        | LO=800MHz, -5dBm; SSB   |
| Maximum Output Power                  | -3            | 0     | +2                    | dBm    | TETRA I&Q Amplitude=2V <sub>pp</sub><br>Over operating temperature.                           |
| High-Linearity Output Power           | -6            | -5    |                       | dBm    | TETRA I&Q Amplitude=1.1V <sub>pp</sub> with an ACPR of<br>-47dBc. Over operating temperature. |
| Adjacent Channel Power Rejection      | -47           | -52   |                       | dBc    | TETRA modulation applied with P <sub>OUT</sub> =-5dBm.<br>Over operating temperature.         |
| Output P1dB                           | +2            | +3    |                       | dBm    | Over operating temperature.   |
| IM3 Suppression                       | -39           | -40   |                       | dBc    | 2kHz offset (9kHz, 11kHz) at -6dBm/tone.<br>Over operating temperature.                       |
| IM5 Suppression                       | -49           | -59   |                       | dBc    | 2kHz offset (9kHz, 11kHz) at -6dBm/tone.<br>Over operating temperature.                       |
| IM7 Suppression                       | -49           | -71   |                       | dBc    | 2kHz offset (9kHz, 11kHz) at -6dBm/tone.<br>Over operating temperature.                       |
| Carrier Suppression                   | -25           | -30   |                       | dBc    | Unadjusted performance.   |
| Sideband Suppression                  | -25           | -30   |                       | dBc    | Unadjusted performance.   |
| Broadband Noise Floor                 |               | -150  | -145                  | dBm/Hz | 26MHz offset with TETRA signal applied<br>P <sub>OUT</sub> =-5dBm.                            |

| Parameter                   | Specification |         |      | Unit   | Condition   |
|-----------------------------|---------------|---------|------|--------|---|
|                             | Min.          | Typ.    | Max. |        |   |
| <b>RF Output (~900MHz)</b>  |               |         |      |        |   |
| Maximum Output Power        | 0             | +4      |      | dBm    | I&Q Amplitude=2V <sub>pp</sub>  |
| High-Linearity Output Power |               | -11     |      | dBm    | I&Q Amplitude=0.325V <sub>pp</sub>  |
| Carrier Suppression         | 50            |         |      | dB     | T=25 °C; P <sub>OUT</sub> =-11dBm (meets CDMA base station requirements); optimized I,Q DC offsets                  |
|                             | 35            |         |      | dB     | Over Temperature (Temperature cycled from -40 °C to +85 °C after optimization at T=25 °C; P <sub>OUT</sub> =-11dBm) |
| Sideband Suppression        | 50            |         |      | dB     | T=25 °C; P <sub>OUT</sub> =-11dBm; optimized I,Q DC offsets   |
|                             | 35            |         |      | dB     | Over Temperature (Temperature cycled from -40 °C to +85 °C after optimization at T=25 °C; P <sub>OUT</sub> =-11dBm) |
| Output Impedance            |               | 13-j:25 |      | Ω      |   |
| Broadband Noise Floor       |               | -153.0  |      | dBm/Hz | At 20MHz offset, V <sub>CC</sub> =5V; Tied to V <sub>REF</sub> : I SIG, Q SIG, I REF, and Q REF.                    |
| <b>RF Output (~2000MHz)</b> |               |         |      |        |   |
| Maximum Output Power        | -7            | -3      |      | dBm    | I&Q Amplitude=2V <sub>pp</sub>  |
| High-Linearity Output Power |               | -17     |      | dBm    | I&Q Amplitude=0.325V <sub>pp</sub>  |
| Carrier Suppression         | 50            |         |      | dB     | T=25 °C; P <sub>OUT</sub> =-17 dBm; optimized I,Q DC offsets  |
|                             | 35            |         |      | dB     | Temperature cycled from -40 °C to +85 °C after optimization at T=25 °C; P <sub>OUT</sub> =-17 dBm                   |
| Sideband Suppression        | 50            |         |      | dB     | T=25 °C; P <sub>OUT</sub> =-17 dBm; optimized I,Q DC offsets  |
|                             | 40            |         |      | dB     | Temperature cycled from -40 °C to +85 °C after optimization at T=25 °C; P <sub>OUT</sub> =-17 dBm                   |
| Output Impedance            |               | 58-j11  |      | Ω      |   |
| Broadband Noise Floor       |               | -158.0  |      | dBm/Hz | At 20MHz offset, V <sub>CC</sub> =5V; Tied to V <sub>REF</sub> : I SIG, Q SIG, I REF, and Q REF.                    |
| <b>Power Down</b>           |               |         |      |        |   |
| Turn On/Off Time            |               |         | 100  | ns     |   |
| PD Input Resistance         | 50            |         |      | kΩ     |   |
| Power Control "ON"          |               |         | 2.8  | V      | Threshold voltage   |
| Power Control "OFF"         | 1.0           | 1.2     |      | V      | Threshold voltage   |
| <b>Power Supply</b>         |               |         |      |        |   |
| Voltage                     |               | 5       |      | V      | Specifications  |
|                             | 4.5           |         | 6.0  | V      | Operating Limits  |
| Current                     |               | 50      |      | mA     | Operating   |
|                             |               |         | 25   | μA     | Power Down  |

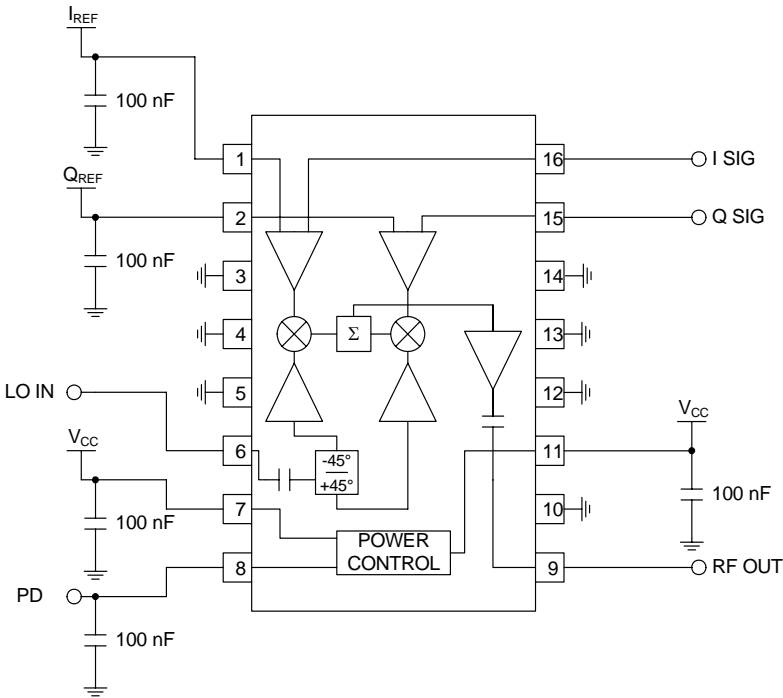
| Pin | Function | Description  | Interface Schematic |
|-----|----------|--|---------------------|
| 1   | I REF    | Reference voltage for the I mixer. This voltage should be the same as the DC voltage supplied to the I SIG pin. A voltage of 3.0V is recommended. The SIG and REF inputs are inputs of a differential amplifier. Therefore the REF and SIG inputs are interchangeable. If swapping the I SIG and I REF pins, the Q SIG and Q REF also need to be swapped to maintain the correct phase. It is also possible to drive the SIG and REF inputs in a balanced mode. This will increase the gain.<br><br>For optimum carrier suppression, the DC voltages on I REF, Q REF, I SIG and Q SIG should be adjusted slightly to compensate for inherent undesired internal DC offsets; for optimum sideband suppression, phase and signal amplitude on IREF, Q REF, I SIG and Q SIG should be adjusted slightly to compensate for inherent undesired internal offsets. See RFMD AN0001 for more detail. |                     |
| 2   | Q REF    | Reference voltage for the Q mixer. This voltage should be the same as the DC voltage supplied to the Q SIG pin. A voltage of 3.0V is recommended. See pin 1 for more details.  |                     |
| 3   | GND2     | Ground connection of the LO phase shift network. This pin should be connected directly to the ground plane.  |                     |
| 4   | GND2     | Same as pin 3.   |                     |
| 5   | GND2     | Same as pin 3.   |                     |
| 6   | LO       | The input of the phase shifting network. This pin has an internal DC blocking capacitor. This port is voltage driven so matching at different frequencies is not required.   |                     |
| 7   | VCC1     | Power supply for all circuits except the RF output stage. An external capacitor is needed if no other low frequency bypass capacitor is nearby.  |                     |
| 8   | PD       | Power Down control. When this pin is "low", all circuits are shut off. A "low" is typically 1.2V or less at room temperature. When this pin is "high" ( $V_{CC}$ ), all circuits are operating normally. If PD is below $V_{CC}$ , output power and performance will be degraded. Operating in this region is not recommended, although it might be useful in some applications where power control is required.   |                     |
| 9   | RF OUT   | RF Output. This pin has an internal DC blocking capacitor. At some frequencies, external matching may be needed to optimize output power.  |                     |
| 10  | GND3     | Ground connection for the RF output stage. This pin should be connected directly to the ground plane.  |                     |
| 11  | VCC2     | Power supply for the RF output amplifier. An external capacitor is needed if no other low frequency bypass capacitor is near by.   |                     |
| 12  | GND1     | Ground connection for the LO and baseband amplifiers, and for the mixers. This pin should be connected directly to the ground plane.   |                     |
| 13  | GND1     | Same as pin 12.  |                     |
| 14  | GND1     | Same as pin 12.  |                     |

| Pin | Function | Description  | Interface Schematic   |
|-----|----------|--|---|
| 15  | Q SIG    | Baseband input to the Q mixer. This pin is DC-coupled. Maximum output power is obtained when the input signal has a peak to peak amplitude of 2V; for highly linear operation, the input signal (and output power) must be reduced appropriately. The recommended DC level for this pin is 3.0V. The peak minimum voltage on this pin ( $V_{REF} - \text{peak modulation amplitude}$ ) should never drop below 2.0V. The peak maximum voltage on this pin ( $V_{REF} + \text{peak modulation amplitude}$ ) should never exceed 4.0V. See pin 1 for more details. |  |
| 16  | I SIG    | Baseband input to the I mixer. This pin is DC-coupled. Maximum output power is obtained when the input signal has a peak to peak amplitude of 2V; for highly linear operation, the input signal (and output power) must be reduced appropriately. The recommended DC level for this pin is 3.0V. The peak minimum voltage on this pin ( $V_{REF} - \text{peak modulation amplitude}$ ) should never drop below 2.0V. The peak maximum voltage on this pin ( $V_{REF} + \text{peak modulation amplitude}$ ) should never exceed 4.0V. See pin 1 for more details. |  |

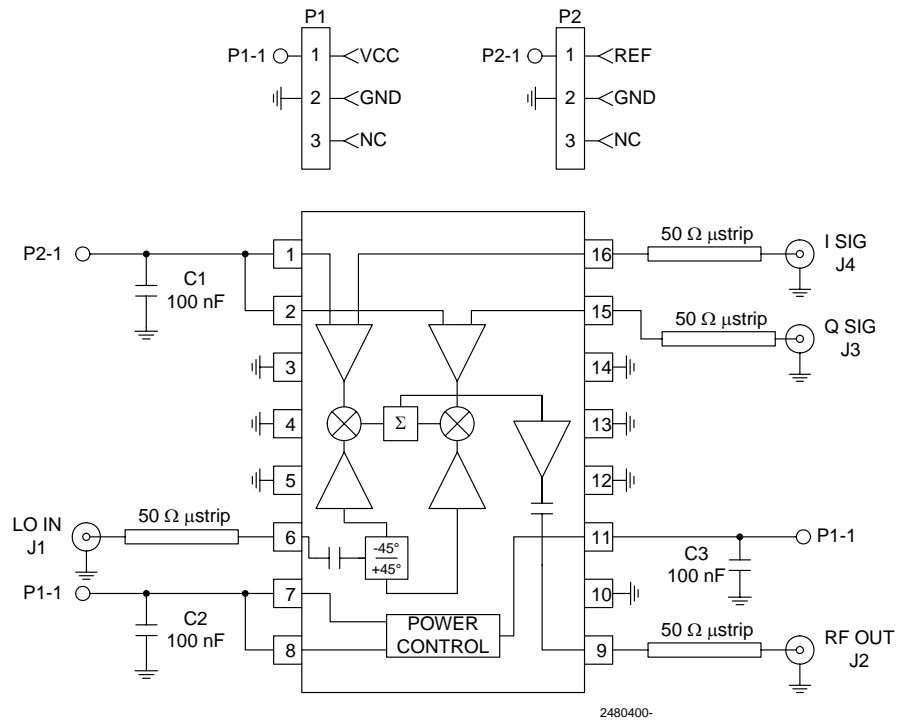
**Package Drawing**



## Application Schematic DC-Coupled



**Evaluation Board Schematic**



## Evaluation Board Layout

Board Size 1.510" x 1.510"  
Board Thickness 0.031", Board Material FR-4

